NPN Silicon Epitaxial Planar Transistor

for switching and amplifier applications. Especially suitable for AF-driver stages and low power output stages.

The transistor is subdivided into four groups, B, C, D and E, according to its DC current gain. As complementary type the PNP transistor ST 8550 is recommended.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

Sym	bol Value	Unit
V _C	_{EO} 25	V
V _C	BO 40	V
V _E	BO 6	V
Ic	800	mA
Ic	м 1	А
I _E	3 100	mA
Pt	ot 625 ¹⁾	mW
Т	j 150	ос
T	-55 to +150	°С
		-55 to +150 nce of 2 mm from case









Characteristics at T_{amb}=25 °C

		Symbol	Min.	Тур.	Max.	Unit
DC Current Gain						
at V_{CE} =1V, I_{C} =100mA	ST 8050B	h_{FE}	70	-	120	-
	ST 8050C	h_{FE}	120	-	200	-
	ST 8050D	h_{FE}	160	-	300	-
	ST 8050E	h _{FE}	300	-	380	-
at V_{CE} =1V, I_{C} =350mA		h_{FE}	60	-	-	-
Collector Cutoff Current						
at V _{CB} =35V		I_{CBO}	-	-	100	nA
Collector Saturation Voltage						
at $I_C=500$ mA, $I_B=50$ mA		$V_{CE(sat)}$	-	-	0.5	V
Base Saturation Voltage						
at $I_C=500$ mA, $I_B=50$ mA		$V_{BE(sat)}$	-	-	1.2	V
Collector Emitter Breakdown Voltag	је					
at I _C =2mA		$V_{(BR)CEO}$	25	-	-	V
Collector Base Breakdown Voltage						
at I _C =10μA		$V_{(BR)CBO}$	40	-	-	V
Emitter Base Breakdown Voltage						
at I _E =100μA		$V_{(BR)EBO}$	6	-	-	V
Gain Bandwidth Product						
at V_{CE} =5V, I_{C} =10mA, f=50MHz		f_T	-	100	-	MHz
Collector Base Capacitance						
at V_{CB} =10V, f=1MHz		C_{CBO}	-	12	-	pF
Thermal Resistance Junction to Am	nbient	R _{thA}	-	-	200 ¹⁾	K/W
1) Valid provided that leads are kep					l.	1







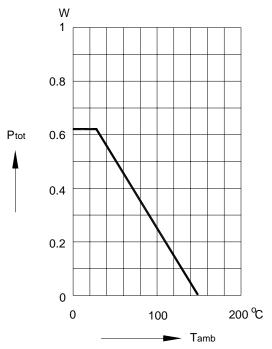


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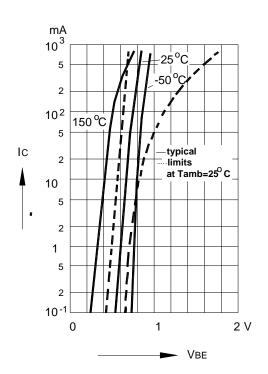
Admissible power dissipation versus ambient temperature

Valid provided that leads are kept at ambient temperature

at a distance of 2 mm from case

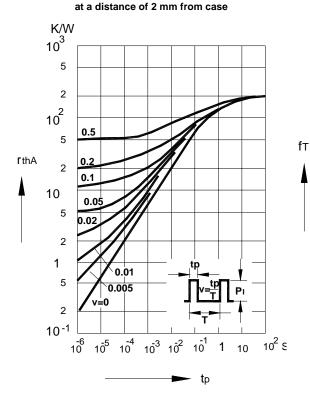


Collector current versus base emitter voltage

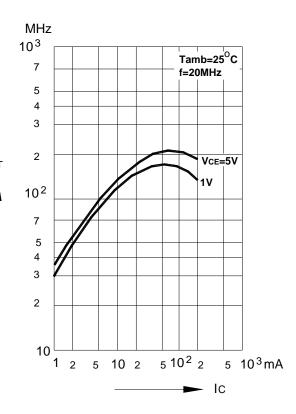


Pulse thermal resistance versus pulse duration

Valid provided that leads are kept at ambient temperature



Gain bandwidth product versus collector current





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Dated: 01/09/2003

VCEsat

0.2

0.1

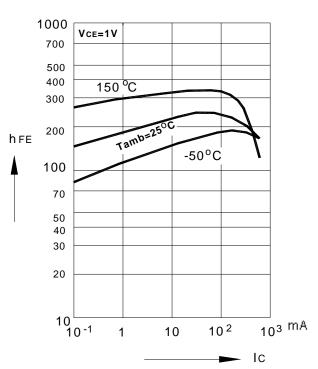
0

10 -1

Collector saturation voltage versus collector current

٧ 0.5 -typical -limits at Tamb=25° C 0.4 =10 0.3

DC current gain versus collector current



Base saturation voltage versus collector current

10

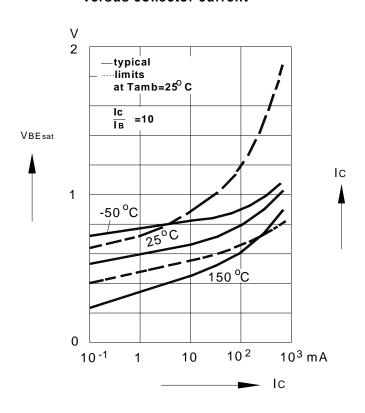
150 °C

-50 °C

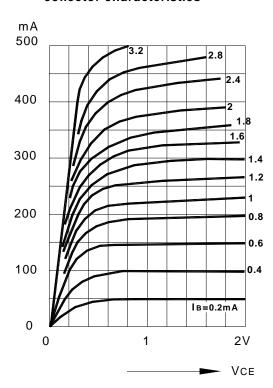
lс

 $10^3 \, mA$

10²



Common emitter collector characteristics





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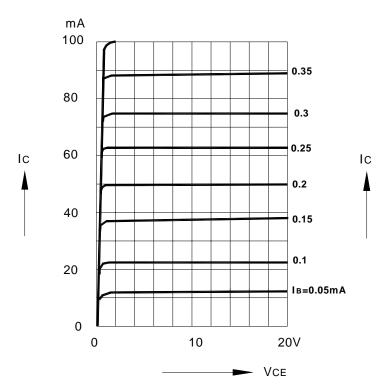
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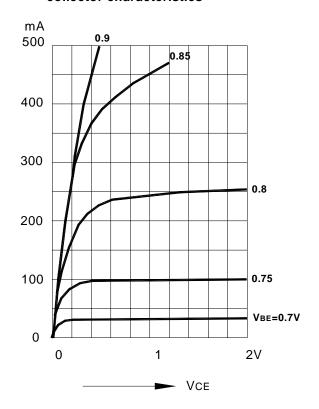




Common emitter collector characteristics



Common emitter collector characteristics





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